

ABSTRACT

A METHOD OF FORMING TOP METAL CONTACT TO ANTIFUSE

A method for fabricating a self-aligned antifuse cell is described. An antifuse is provided overlying a metal plug in an insulating layer on a semiconductor substrate. A dielectric layer is deposited overlying the antifuse. The dielectric layer is etched to form dielectric spacers on the sidewalls of the antifuse. A top metal layer is deposited overlying the antifuse and dielectric spacers and patterned to complete the antifuse cell in an integrated circuit device.

(FIGURE 3 IS SUGGESTED FOR PUBLICATION)